Amendments to the Claims

1. (previously presented) A method for manufacturing a light emitting diode having a transparent substrate, the method comprising:

forming a semiconductor multilayer on a first substrate producing a first multilayer structure;

forming a conductive amorphous interface layer on a second substrate, the second substrate being transparent in nature, producing a second multilayer structure;

bonding the first multilayer structure to the second multilayer structure, producing a third multilayer structure; and

removing the first substrate from the third multilayer structure.

2. (original) The method of claim 1 further comprising a step of forming a transparent conductive layer on the third multilayer structure after removing the first substrate.

3. (previously presented) The method of claim 1, wherein the amorphous interface layer is made of at least one selected from a group consisting of indium tin oxide, indium cadmium oxide, antimony tin oxide, and transparent adhesive agent.

4. (previously presented) A method for manufacturing a light emitting diode, comprising:

forming a semiconductor multilayer on a first substrate producing a first multilayer structure;

forming a conductive amorphous interface layer on a second substrate, the second substrate being transparent in nature, producing a second multilayer structure;

bonding the first multilayer structure to the second multilayer structure, producing a third multilayer structure; and

removing the first substrate from the third multilayer structure.

5. (original) The method of claim 4 further comprising a step of forming a transparent conductive layer on the third multilayer structure after removing the first substrate.

6. (previously presented) The method of claim 4, wherein the amorphous interface layer is made of at least one selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, and transparent adhesive agent.

7. (new) The method of claim 1 further comprising etching away a portion of the first multilayer structure to partially expose the amorphous interface layer.